

Silicon PNP Power Transistors

2SB668

DESCRIPTION

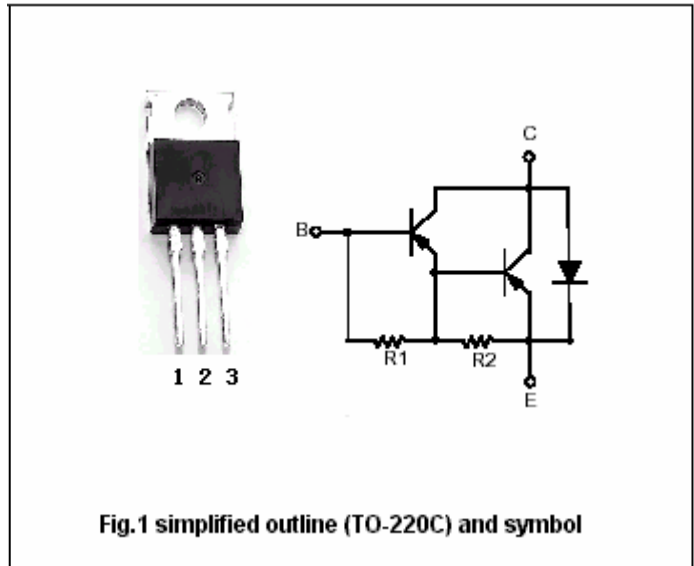
- With TO-220C package
- High DC current gain
- DARLINGTON

APPLICATIONS

- For use in power amplifier and switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector; connected to mounting base
3	Emitter



Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-100	V
V _{CEO}	Collector-emitter voltage	Open base	-100	V
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current		-3	A
I _{CM}	Collector current-peak		-5	A
P _C	Collector power dissipation	T _C =25	25	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

Silicon PNP Power Transistors

2SB668

CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-10mA, I _B =0	-100			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =-1mA, I _E =0	-100			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-2mA, I _C =0	-5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-2A, I _B =-8mA			-2.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-2A, I _B =-8mA			-2.5	V
I _{CBO}	Collector cut-off current	V _{CB} =-120V, I _E =0			-100	μ A
I _{CEO}	Collector cut-off current	V _{CE} =-100V, I _B =0			-500	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =-5V, I _C =0			-2	mA
h _{FE}	DC current gain	I _C =-1A; V _{CE} =-3V	2000			

PACKAGE OUTLINE

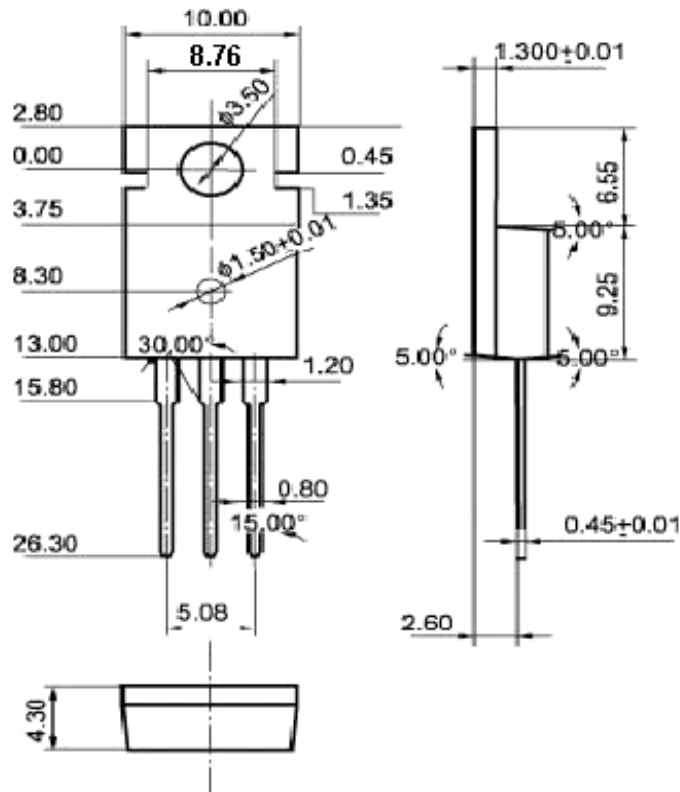


Fig.2 Outline dimensions